

# SSC8333GS1

#### **Dual P-Channel Enhancement Mode MOSFET**

Features

VDS	VGS	RDSON Typ.	ID
-30V	±20V	61mR@-10V	4 5 4
		77mR@-4V5	-4.5A

## > Description

This device is produced with high cell density, DMOS trench technology, which is especially used to minimize on-state resistance. This device is particularly suited for low voltage power management requiring a wild range of given voltage ratings(4.5V~25V) such as load switch and battery protection.

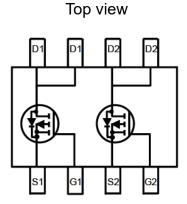
## > Applications

- TFT panel power switch
- High Side DC/DC Converter
- High Side Driver for Brushless
  DC motor
- Portable DVD, DPF

#### Ordering Information

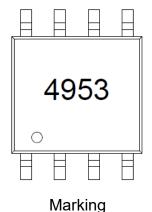
Device	Package	Shipping
SSC8333GS1	SOP-8	4000/Reel

Pin configuration





Bottom View





#### > Absolute Maximum Ratings(T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V <sub>DSS</sub>	Drain-to-Source Voltage	-30	V
V <sub>GSS</sub>	Gate-to-Source Voltage	±20	V
Ι <sub>D</sub>	Continuous Drain Current <sup>a</sup>	-4.5	А
I <sub>DM</sub>	Pulsed Drain Current <sup>b</sup>	-20	А
PD	Power Dissipation <sup>c</sup>	2	W
P <sub>DSM</sub>	Power Dissipation <sup>a</sup>	1.2	W
TJ	Operation junction temperature	-55 to 150	°C
T <sub>STG</sub>	Storage temperature range	-55 to 150	°C

## > Thermal Resistance Ratings(T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
R <sub>0JA</sub>	Junction-to-Ambient Thermal Resistance <sup>a</sup>		110	°C 0.0
R <sub>θJC</sub>	Junction-to-Case Thermal Resistance		70	°C/W

Note:

- a. The value of RθJA is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper,in a still air environment with TA=25°C.The value in any given application depends on the user is specific board design. The current rating is based on the t≤ 10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation PD is based on TJ(MAX)=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

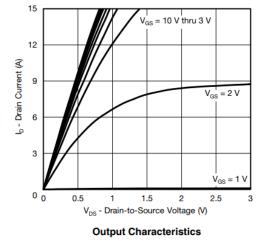


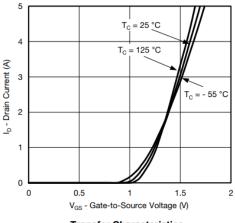
# Electronics Characteristics(T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур.	Мах	Unit
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	VGS=0V,ID=-250uA	-30			V
$V_{GS \ (th)}$	Gate Threshold Voltage	VDS=VGS,ID=-250uA	-1	-1.4	-3	V
	Drain-Source On-	VGS=-10V,ID=-6A		61	70	mR
$R_{DS(on)}$	Resistance	VGS=-4.5V,ID=-4A		77	85	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	VDS=-24V,VGS=0V			-1	uA
I <sub>GSS</sub>	Gate-Source leak current	VGS=±20V,VDS=0V			±100	nA
V <sub>SD</sub>	Forward Voltage	VGS=0V,IS=-1A		-0.8	-1.5	V
G <sub>FS</sub>	Transconductance	VDS=-5V , ID=3.6A		5		S
Ciss	Input Capacitance	VDS=-15V, VGS=0V, f=1MHz		550		
Coss	Output Capacitance			60		. pF
Crss	Reverse Transfer Capacitance			50		
T <sub>D(ON)</sub>	Turn-on delay time			9		
Tr	Rise time	VGS=-10V,		6		20
$T_{D(OFF)}$	Turn-off delay time	VDS=-15V, RG=3R,RL=2.5R		28		ns
Tf	Fall time			4		
Qg	Total Gate charge			13		
Qgs	Gate to Source charge	VGS=-4.5V , VDS=-15V , ID=-3A		1.6		nC
Qgd	Gate to Drain charge			1.5		

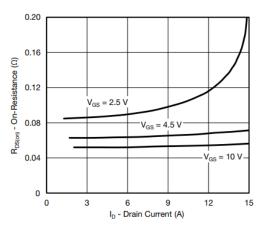


# > **Typical Characteristics**(T<sub>A</sub>=25°C unless otherwise noted)

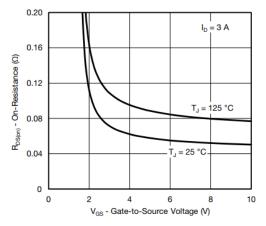




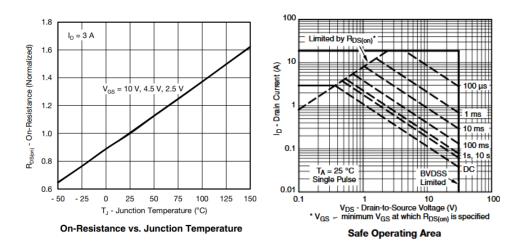
Transfer Characteristics



On-Resistance vs. Drain Current and Gate Voltage

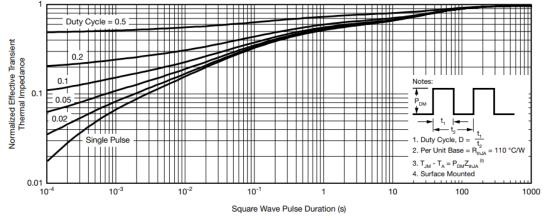


On-Resistance vs. Gate-to-Source Voltage





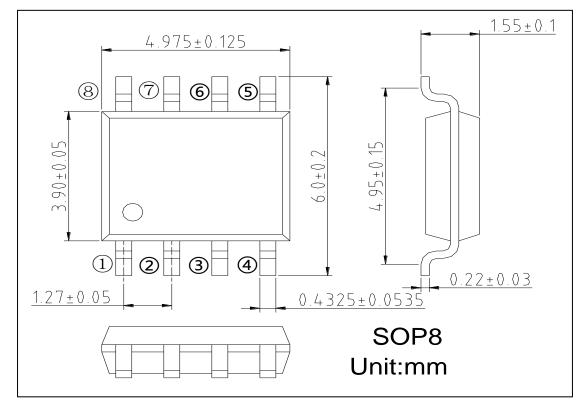
# SSC8333GS1



Normalized Thermal Transient Impedance, Junction-to-Ambient



#### > Package Information



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